

**Silicon NPN Power Transistors**

**2SC3794 2SC3794A**

**DESCRIPTION**

- With TO-220Fa package
- High  $V_{CBO}$
- High speed switching
- Low collector saturation voltage

**APPLICATIONS**

- For high speed switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

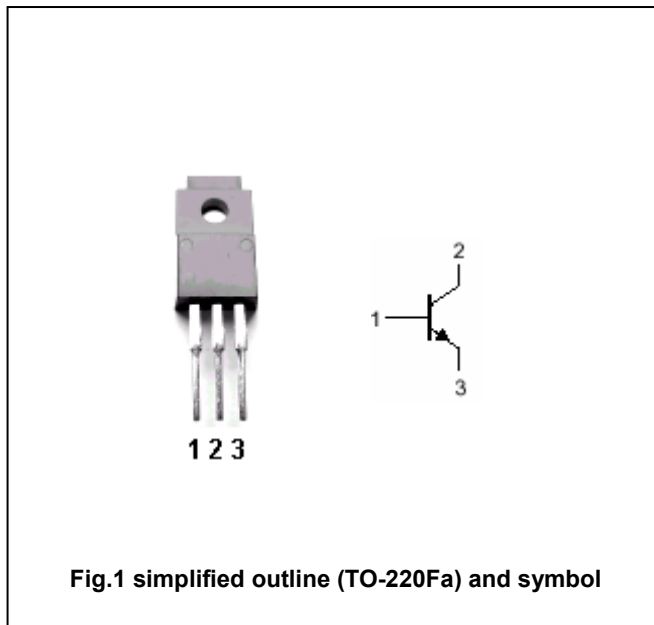


Fig.1 simplified outline (TO-220Fa) and symbol

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2SC3794	800	V
		2SC3794A	900	
$V_{CEO}$	Collector-emitter voltage	Open base	500	V
$V_{EBO}$	Emitter-base voltage	Open collector	8	V
$I_C$	Collector current (DC)		1.5	A
$I_{CM}$	Collector current-Peak		3.0	A
$I_B$	Base current		0.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ C$	25	W
		$T_a=25^\circ C$	2	
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.2A, L=25mH	500			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	2SC3794			0.1	mA
		2SC3794A				
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.1A; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	8			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.2A; V <sub>CE</sub> =10V		8		MHz

## Switching times

t <sub>on</sub>	Turn-on time	2SC3794				1.0	μs
		2SC3794A				1.2	
t <sub>s</sub>	Storage time		I <sub>C</sub> =1A; I <sub>B1</sub> =-I <sub>B2</sub> =0.2A V <sub>CC</sub> =200V			3.0	μs
t <sub>f</sub>	Fall time	2SC3794				1.0	μs
		2SC3794A				1.2	

